

**AMENDMENTS TO THE SPECIFICATION:**

Please replace the title with the following amended title:

**METHOD OF CLEANING A CVD DEVICE APPARATUS**

Please replace paragraph [0045] with the following amended paragraph:

[0045] The vacuum vessel 12 is configured, from the point of view of improving its assembly properties, of an upper vessel 12a which forms the plasma-generating space 15 and a lower vessel ~~24b~~ 12b which forms the film-deposition processing space 16. When the vacuum vessel 12 is formed by assembling the upper vessel 12a and lower vessel 12b, the electrically conductive partition plate 14 is installed between the two. In order to ensure that it is placed at ground potential, the partition plate 14 is mounted so as to make contact with the electrically conductive material fixing part 22, in the manner as shown in figure 3(a), for example. In this way, the separated plasma-generating space 15 and film-deposition processing space 16 are formed on the upper and lower sides of the partition plate 14 and the plasma-generating space 15 is formed by means of the partition plate 14 and upper vessel 12a.

Please replace paragraph [0074] with the following amended paragraph:

[0074] In addition, in cases where fluoride gas is used as the cleaning gas, the adsorption of fluorine onto the inner circumferential face of the through-holes 25 and

the surface of the partition plate must be prevented, and depending on the type of fluoride gas used as the cleaning gas, it is desirable to heat the partition plate 14 to 200°C or more by means of the heater 30, when fluorocarbon gas such as CF<sub>4</sub>, C<sub>2</sub>F<sub>6</sub>, C<sub>3</sub>F<sub>8</sub> or nitrogen fluoride gas such as NF<sub>3</sub> are used, for example. Or, it is desirable to heat the ~~substrate~~ partition plate 14 to a temperature of 100°C or more in cases when using fluoro sulfur gas such as SF<sub>6</sub>, while carrying out said cleaning process.